

60V N-Channel Power MOSFET

DESCRIPTION

The IRFZ44NS uses advanced trench technology to provide excellent RDS(ON), low gate charge. It can be used in a wide variety of applications.

Application

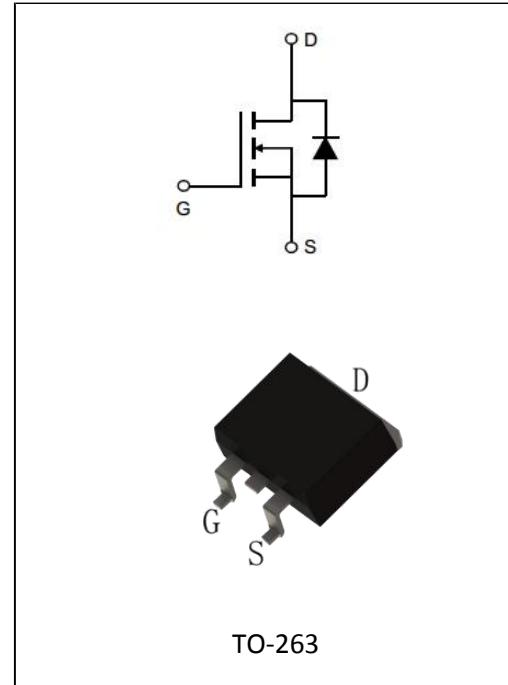
- ① Power switching application
- ② Hard switched and High frequency circuits
- ③ Uninterruptible power supply

KEY CHARACTERISTICS

- ① $V_{DS} = 60V, I_D = 60A$
 $R_{DS(ON)} < 15m\Omega @ V_{GS}=10V$
- ② High density cell design for lower Rdson
- ③ Fully characterized avalanche voltage and current
- ④ Good stability and uniformity with high EAS
- ⑤ Excellent package for good heat dissipation

100% UIS TESTED !

100% DVDS TESTED !



package Marking And Ordering Information:

Ordering Codes	Package	Product Code	Packing
IRFZ44N-S	TO-263	IRFZ44	Reel

Absolute Maximum Ratings (TA=25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	60	A
Drain Current-Pulsed (Note 1)	I_{DM}	200	A
Maximum Power Dissipation($T_c=25^\circ C$)	P_D	87	W
Single pulse avalanche energy(Note 2)	EAS	120	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	1.72	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-Source On-State Resistance ^(Note 3)	R _{D(S)}	V _{GS} =10V, I _D =25A	-	12	15	mΩ
Forward Transconductance	g _{FS}	V _{DS} =25V, I _D =25A	-	25	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	910	-	pF
Output Capacitance	C _{oss}		-	100	-	pF
Reverse Transfer Capacitance	C _{rss}		-	30	-	pF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =20A, V _{GS} =10V, R _{GEN} =5Ω	-	26	-	nS
Turn-on Rise Time	t _r		-	6	-	nS
Turn-Off Delay Time	t _{d(off)}		-	52	-	nS
Turn-Off Fall Time	t _f		-	7	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =50A V _{GS} =10V	-	31	-	nC
Gate-Source Charge	Q _{gs}		-	9	-	nC
Gate-Drain Charge	Q _{gd}		-	5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =50A	-	-	1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. EAS condition :T_j=25°C, V_{DD}=30V, V_{GS}=10V, L=0.5mH, R_g=25Ω
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production.

Characteristics Curves

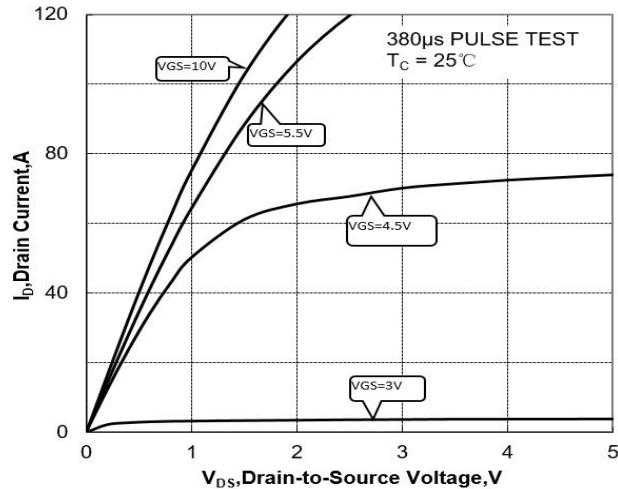
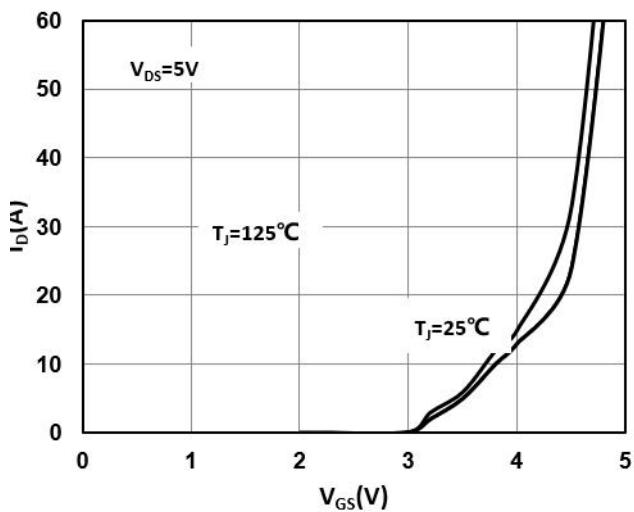
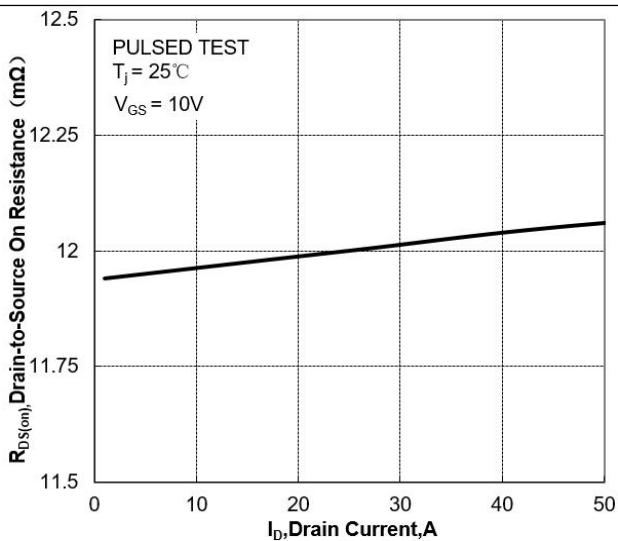
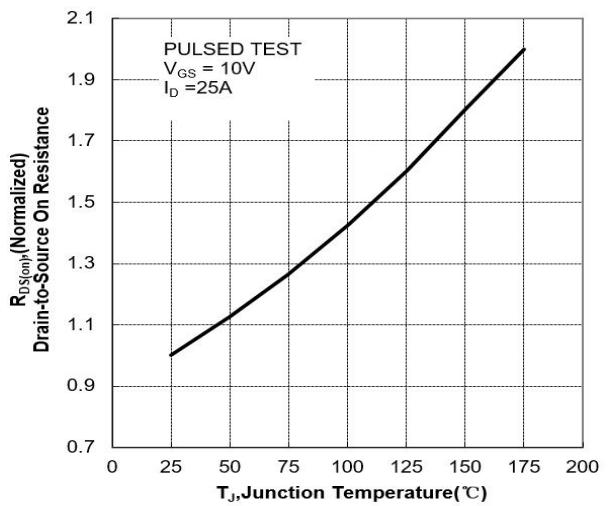
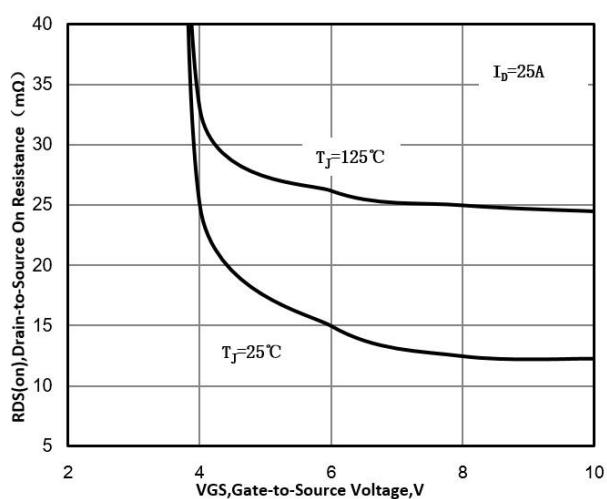
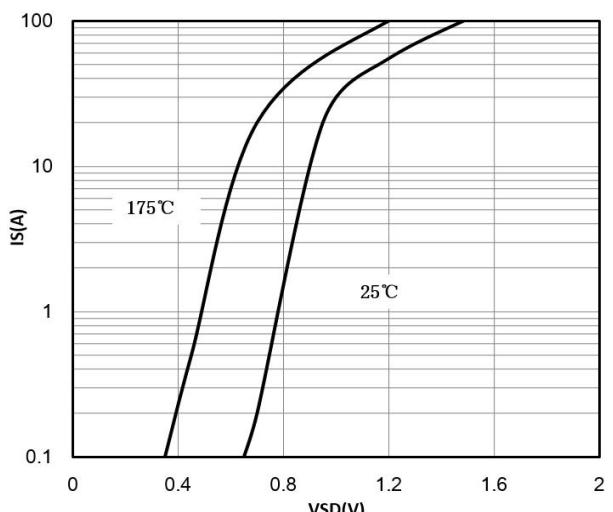
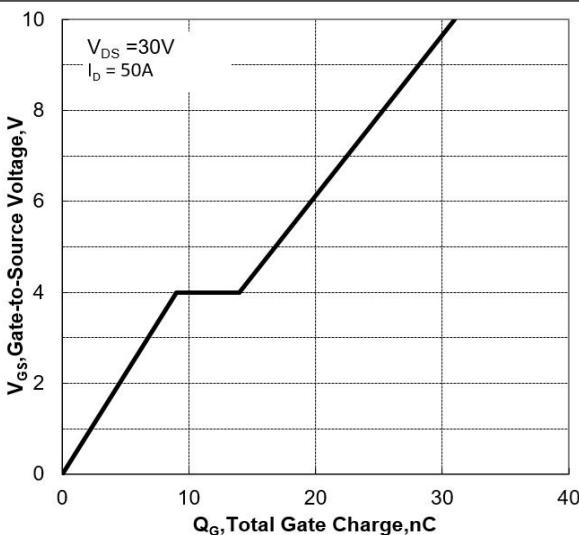
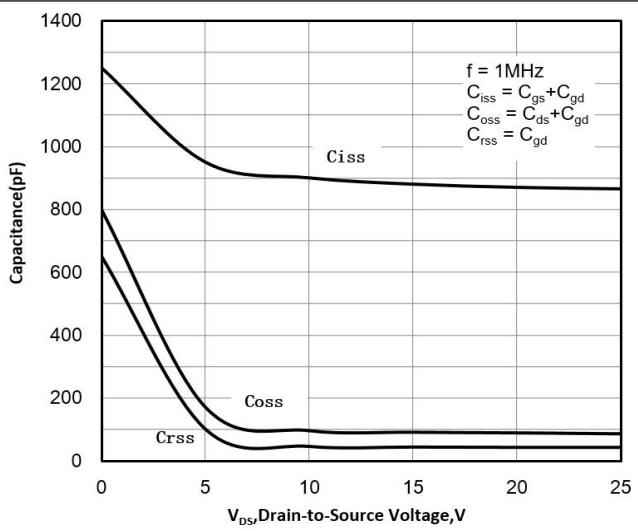
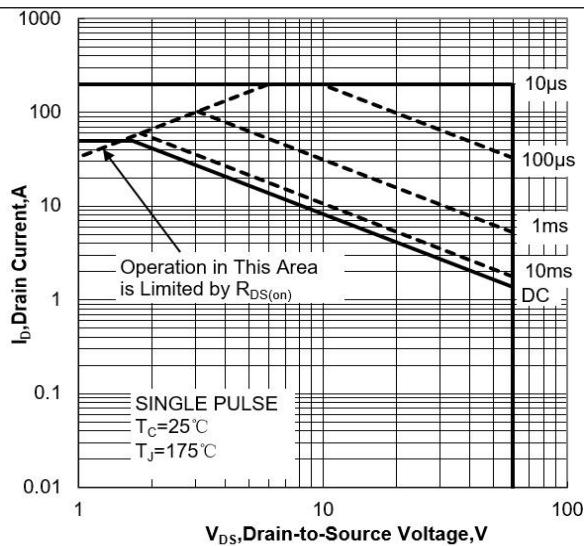
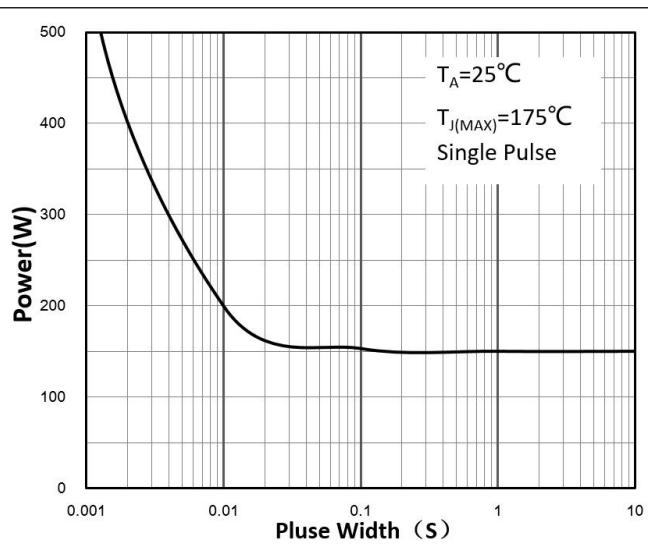
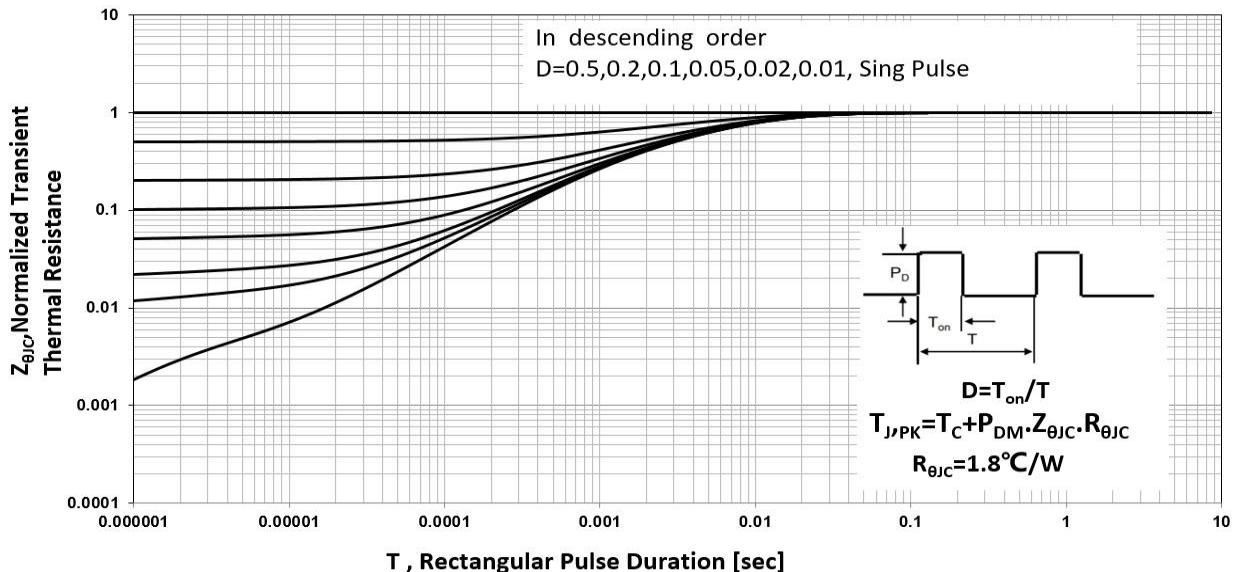
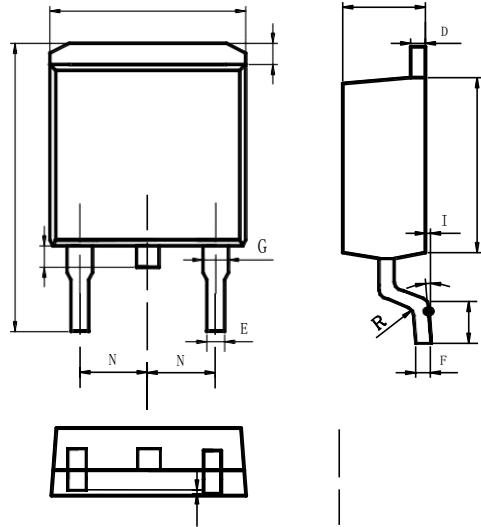
Figure 1 Output Characteristics

Figure 2 Transfer Characteristics

Figure 3 On-Resistance vs. ID and VGS

Figure 4 On-Resistance vs. Junction Temperature

Figure 5 On-Resistance vs. VGS

Figure 6 Body Diode Forward Voltage


Figure 7 Gate-Charge Characteristics

Figure 8 Capacitance Characteristics

Figure 9 Maximum Forward Biased Safe Operation Area

Figure 10 Single Pulse Power Rating Junction-to-Ambient

Figure 11 Normalized Maximum Transient Thermal Impedance


Test Circuit and Waveform

Gate Charge Test Circuit	Gate Charge Test Waveform
Resistive Switching Test Circuit	Resistive Switching Test Waveforms
Unclamped Inductive Switching (UIS) Test Circuit	Unclamped Inductive Switching (UIS) Test Waveforms
Diode Recovery Test Circuit	Diode Recovery Test Waveforms

Package Description



Items	Values(mm)	
	MIN	MAX
A	9.60	10.6
B	15.0	16.0
B1	8.90	9.50
C	4.30	4.80
C1	2.30	3.10
D	1.20	1.40
E	0.70	0.90
F	0.30	0.60
G	1.17	1.37
H	2.70	3.80
L	12.6	14.8
N	2.34	2.74
Q	2.40	3.00
Φ P	3.50	3.90

TO-263 package



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NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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